

# NPN SILICON HI FREQUENCY TRANSISTOR

**DESCRIPTION:**

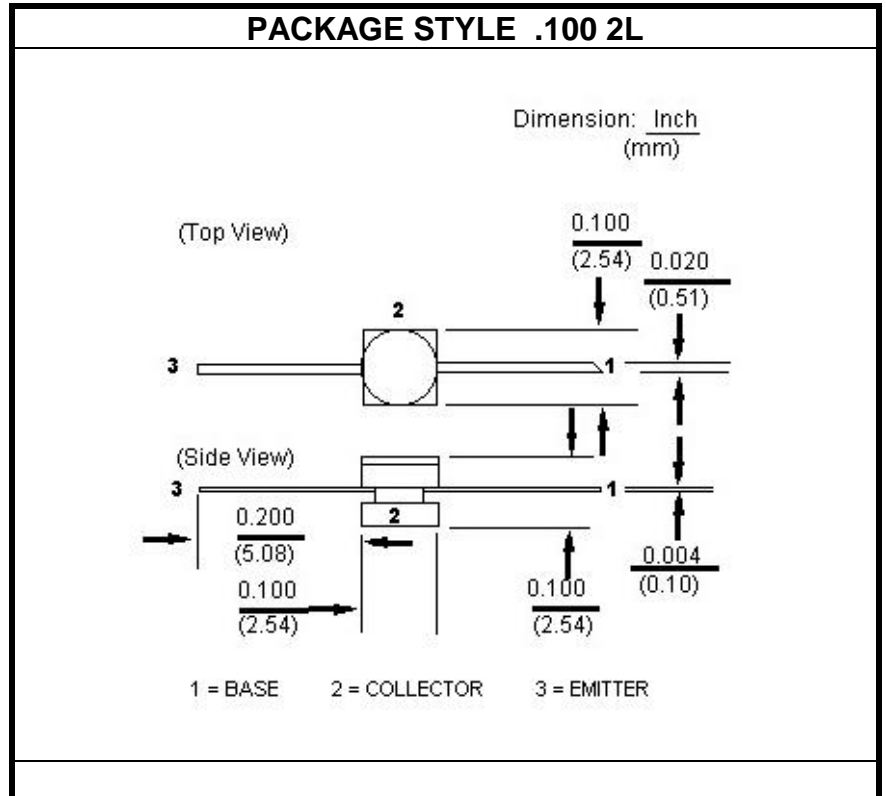
The **ASI NE56787** is Designed for general purpose and ultra linear small signal amplifier applications up to 4.0 GHz.

**FEATURES INCLUDE:**

- Ideal for linear Class-A amplifiers

**MAXIMUM RATINGS:**

$I_C$	60 mA
$V_{CBO}$	25 V
$V_{CEO}$	12 V
$V_{EBO}$	2.0 V
$P_{DISS}$	600 mW @ $T_A \leq 75^\circ C$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +200 °C
$\theta_{JC}$	40 °C/W


**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$I_{CBO}$	$V_{CB} = 10 V$			1.0	$\mu A$
$I_{EBO}$	$V_{EB} = 1.0 V$			1.0	$\mu A$
$h_{FE}$	$V_{CE} = 10 V$ $I_C = 30 mA$	30	100	200	---
$C_{OB}$	$V_{CB} = 10 V$ $f = 1.0 MHz$		0.44	0.80	pF
$f_s$	$ S_{21} ^2 = 0 dB$	7.5	8.0		GHz